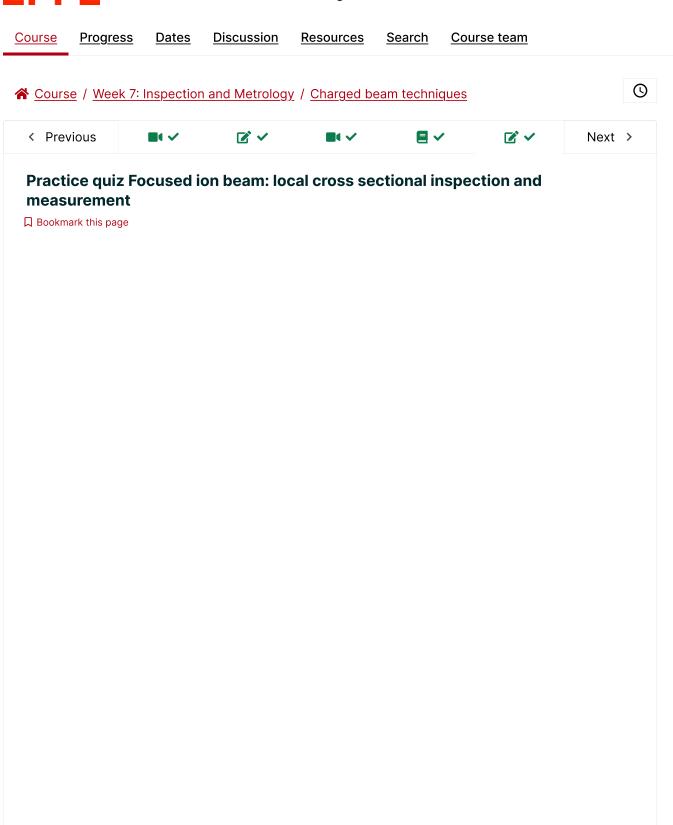


Help 😝~



## Questions:

0 points possible (ungraded)

1. Which of the following statements correctly describe the focused ion beam (FIB) technique?

O In the sputtering mode of the FIB, a high electron beam current is used to remove material from the sample.

The milling mode is used to remove material with better spatial precision and slower rate.

Unlike scanning electron microscopy, there is no need for a conductive surface for FIB imaging.

FIB is a non-invasive technique, which allows inspecting a multilayer device in its z dimension.



## **Explanation**

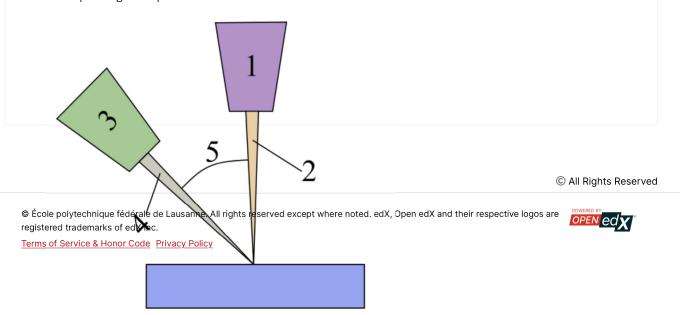
Focused ion beam is a technique in which positively charged ions are used to remove material from a surface. In its sputtering mode, a high ion current is used for fast removal of the material. To obtain smoother cross sections, a polishing step, which is called milling, is essential. The milling mode removes material from the surface with slower rate.

As for SEM, it is better to perform FIB on a conducting sample.

FIB allows removing locally material and therefore it is an invasive technique.

For further information, please see video "Focused ion beam: local cross sectional inspection and measurement" at 01:27.

2. The image below is a scheme of a dual-beam FIB/SEM system. Match the components with the corresponding description



1:

FIB pole ✓ Answer: FIB pole

2:

Ion beam ✓ Answer: Ion beam

